DSE CLASS

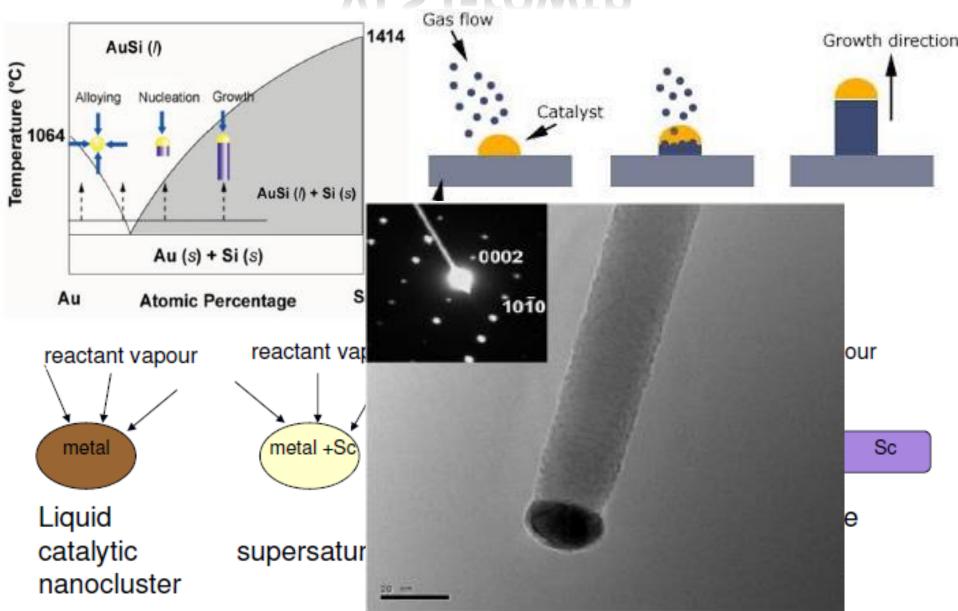
CONDENSED M&TTER PHYSICS

Lecture-13

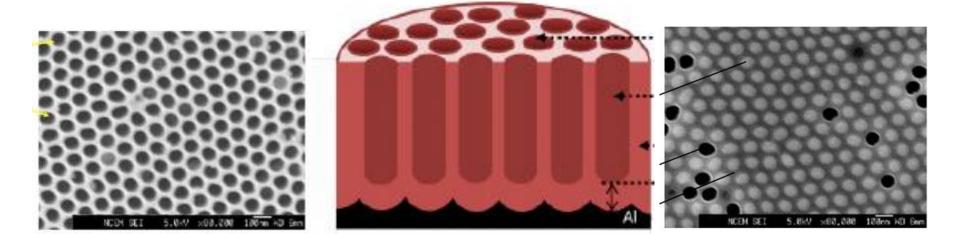
14/1/2021

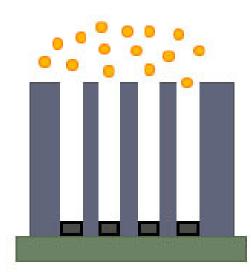
Nanowire Growth

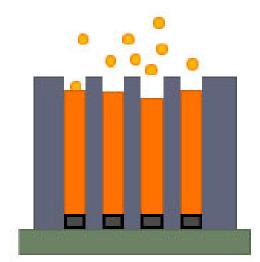
VLS Growth

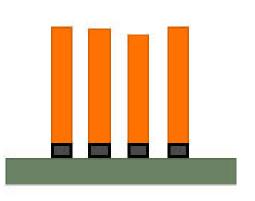


Nanoporous Alumina Template

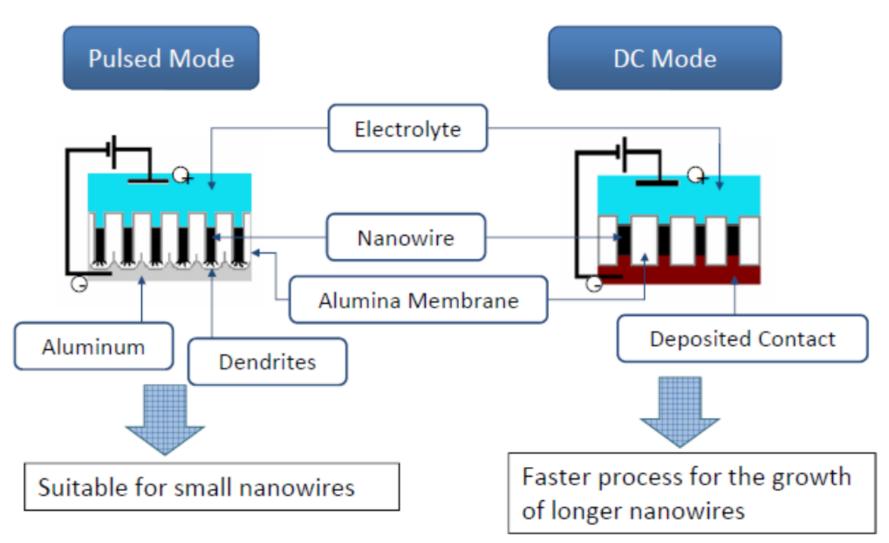








Electrodeposition



Nanoparticle Synthesis

Sol-gel Method:

This method involves two types of materials 'Sol' and 'Gel'

Principle:

•Sol-Gel method involves formation of 'sols' in a liquid and then connecting the sol particles to form a network.

•By drying the liquid, it is possible to obtain powders, thin films etc.,

Methods for sol-gel formation:

Sol can be obtained by,

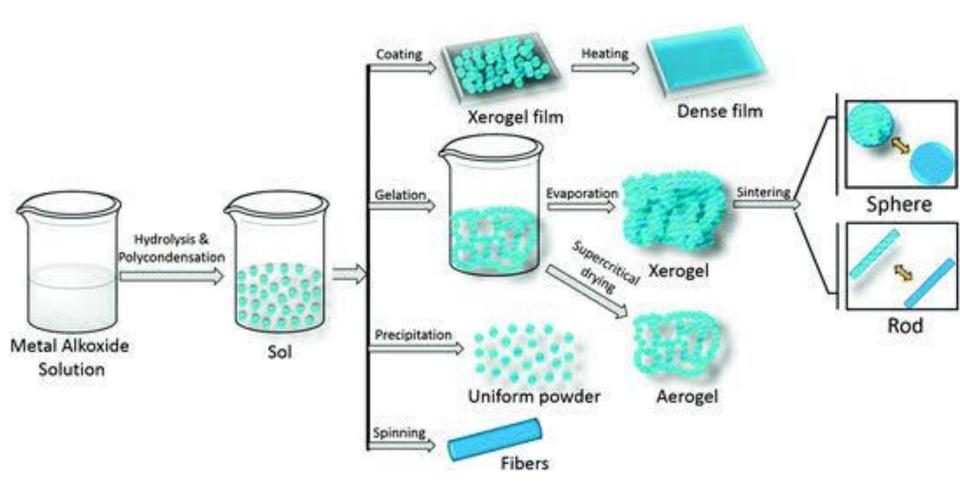
•Hydrolysis

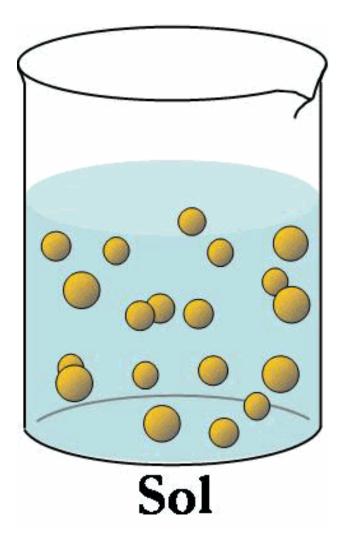
Condensation and Polymerization of monomers to form particles

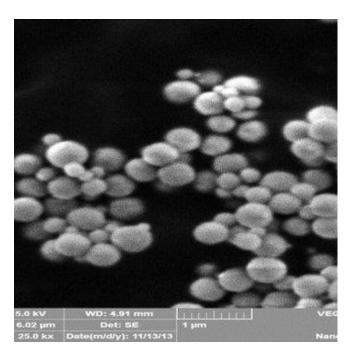
Agglomeration of particles

After the formation of sol, formation of network (gelation) which extends throughout the liquid medium is obtained to form a gel.

Sol-Gel Process



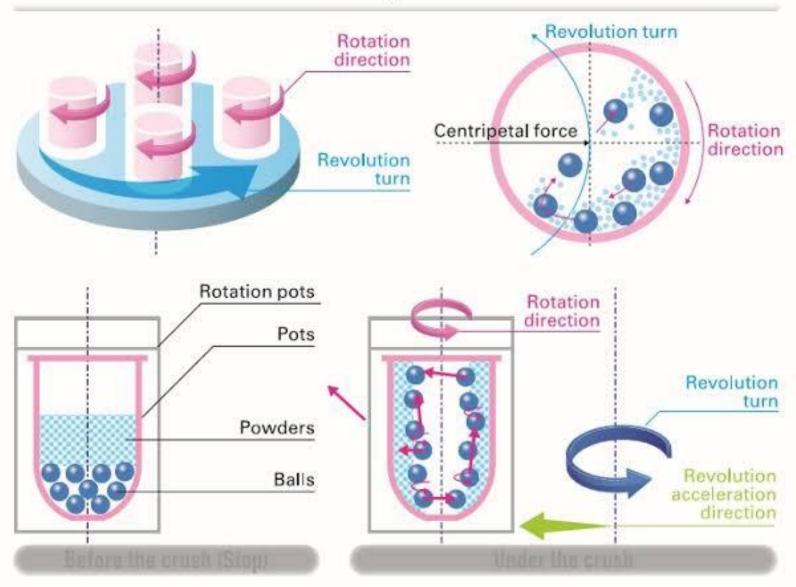




The advantages of using sol-gel processing instead of high temperature processing methods are:

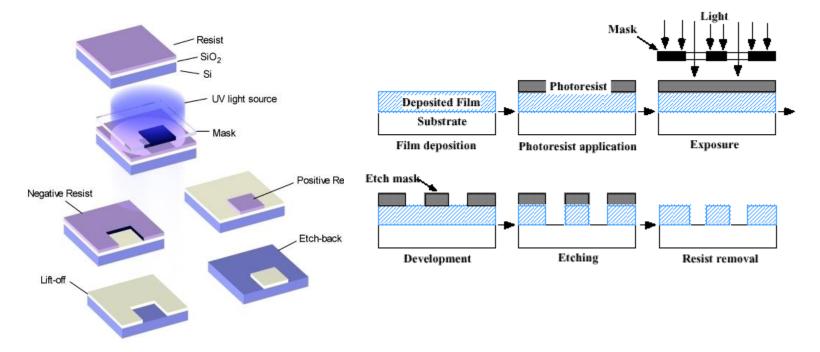
- Iower synthesis temperature
- \succ high purity
- \blacktriangleright novel materials
- \succ low capital costs

Planetary Ball Mill



Lithography

We have discussed various routes for the synthesis and fabrication of variety of nanomaterials; however, the synthesis routes applied have been focused mainly on the chemical methods approaches, or the physical vapor deposition. Now, we will discuss a different approach: top-down approach, fabrication of nanoscale structures with various physical techniques---lithography.



Lithography Process

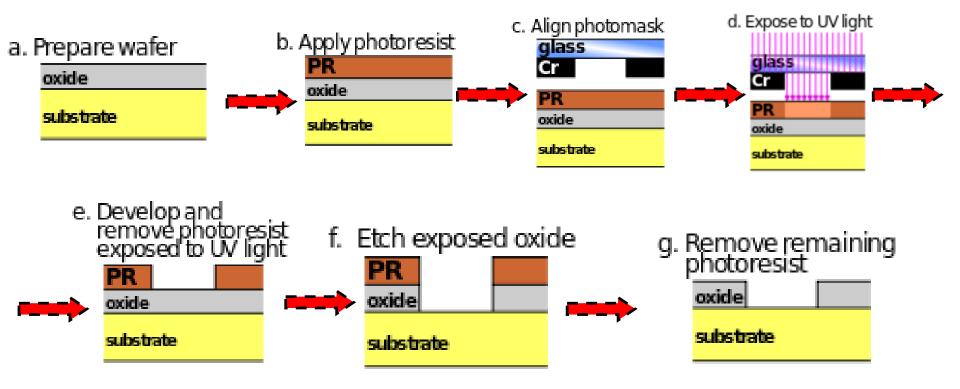
The term is more generally applied to a number of methods for replicating a predetermined master pattern on a substrate.

Basic Steps of Lithography

- Spin coat radiation sensitive polymer Resist
- Expose layer (through mask or direct write)
- Develop
- Etch away or deposit material

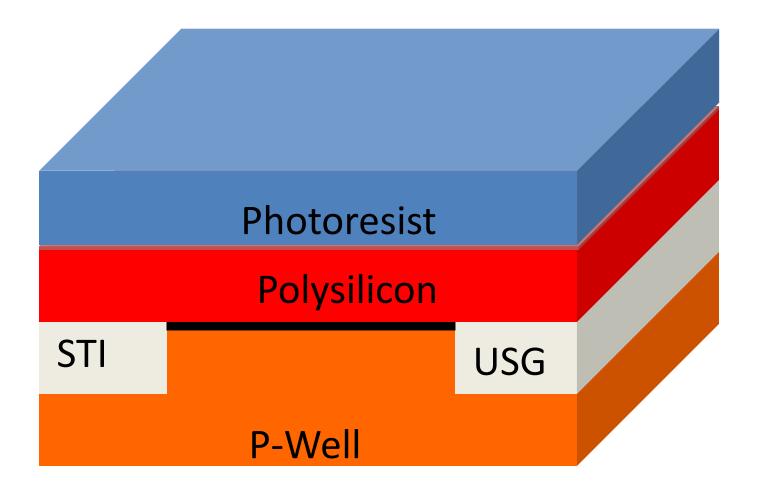
Photolithography

Typical photolithographic process consists of producing a mask carrying the requisite pattern information and subsequently transferring that pattern, using some optical technique into a photoactive polymer or photoresist.



Wafer Clean Gate Oxide Polysilicon STI USG **P-Well**

Photoresist Coating



Photoresist

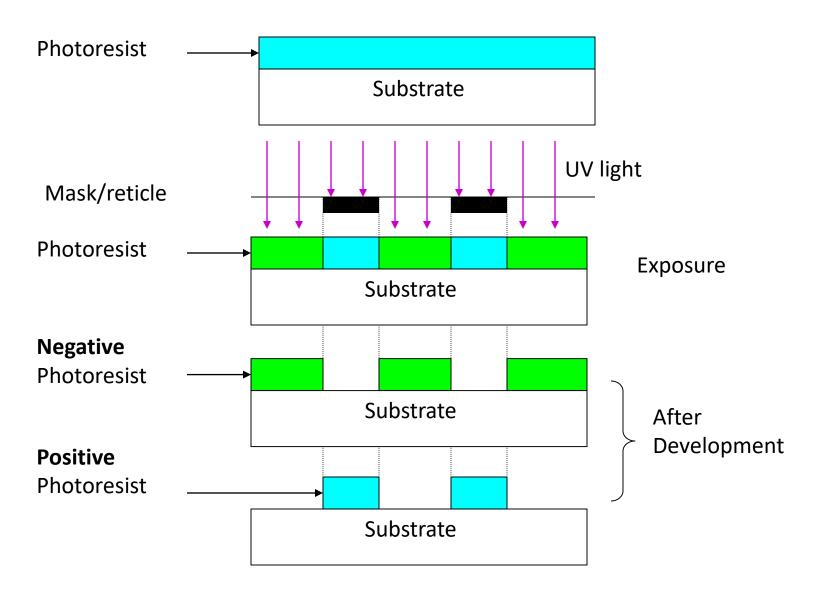
Negative Photoresist

- Becomes insoluble after exposure
- When developed, the unexposed parts dissolved.
- Cheaper

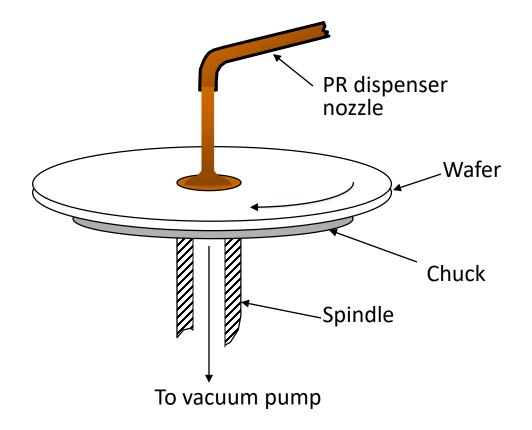
Positive Photoresist

- Becomes soluble after exposure
- When developed, the exposed parts dissolved
- Better resolution

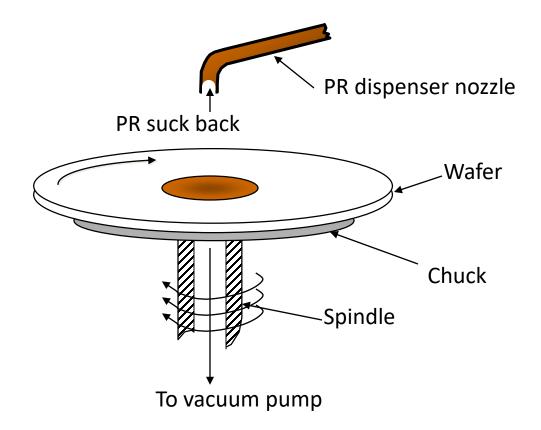
Negative and Positive Photoresists



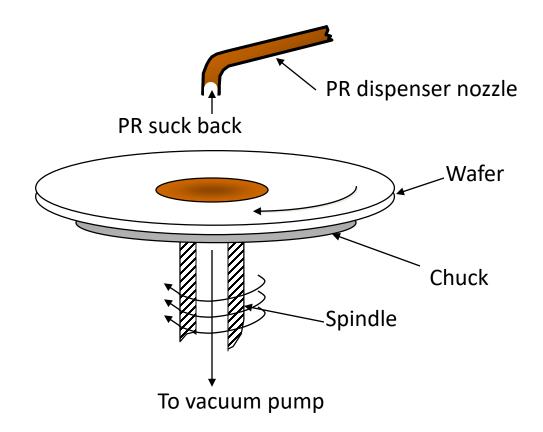
Photoresist Applying

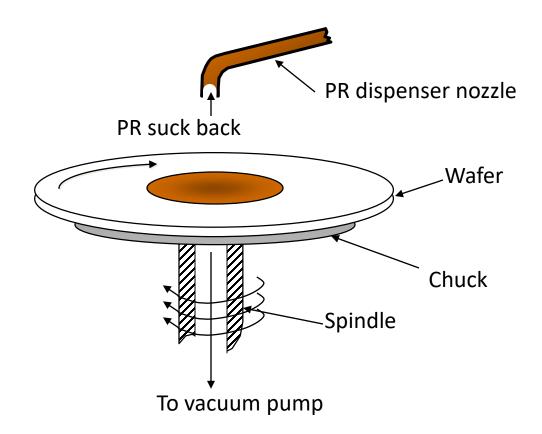


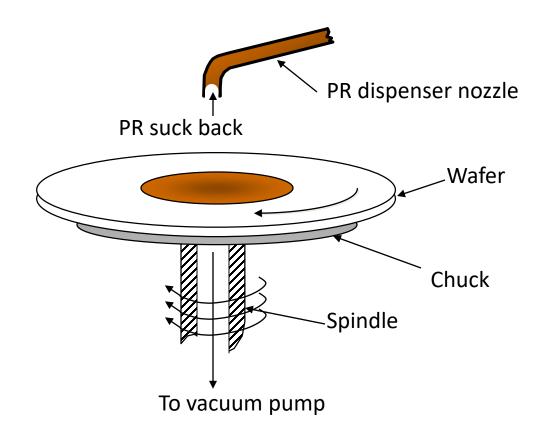
Photoresist Suck Back

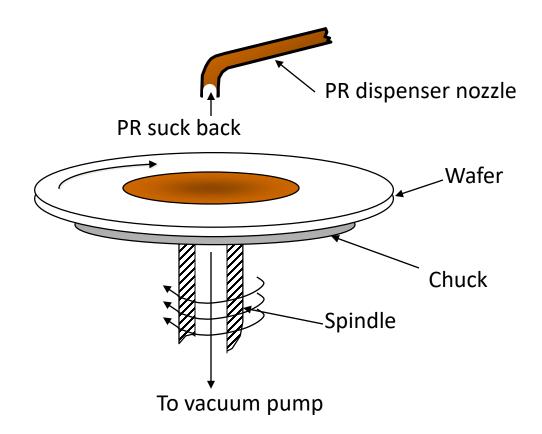


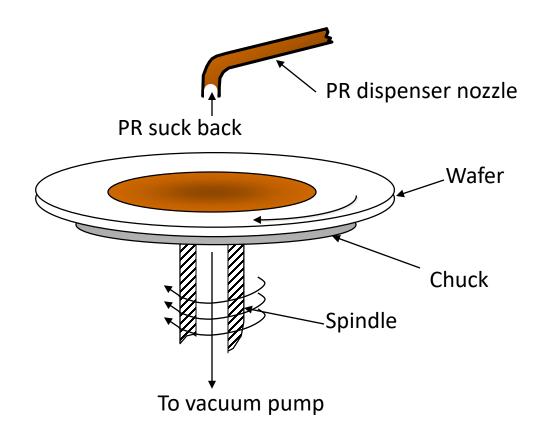
Photoresist Spin Coating

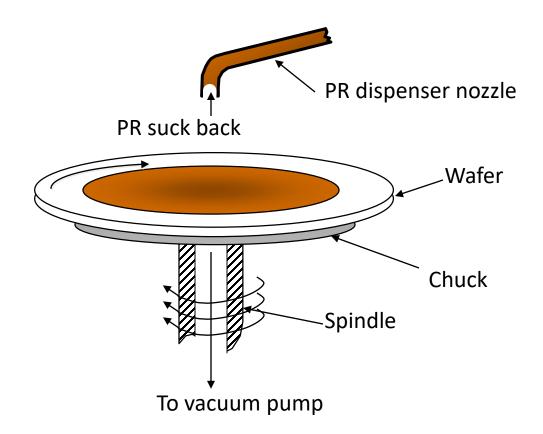


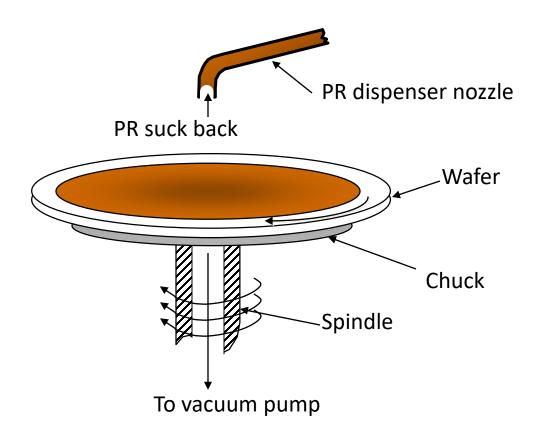


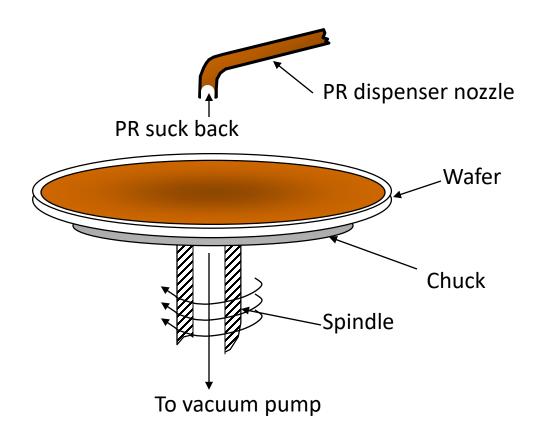


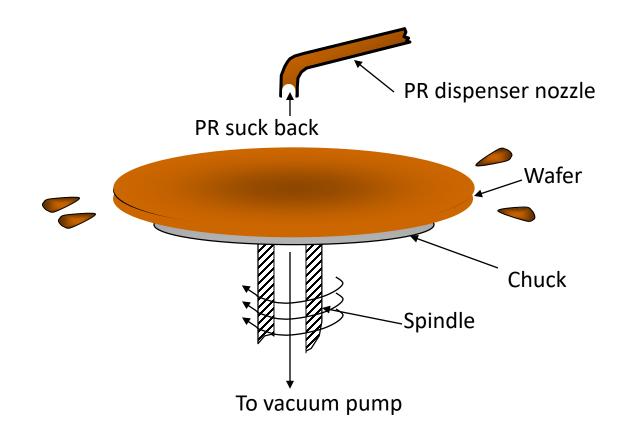


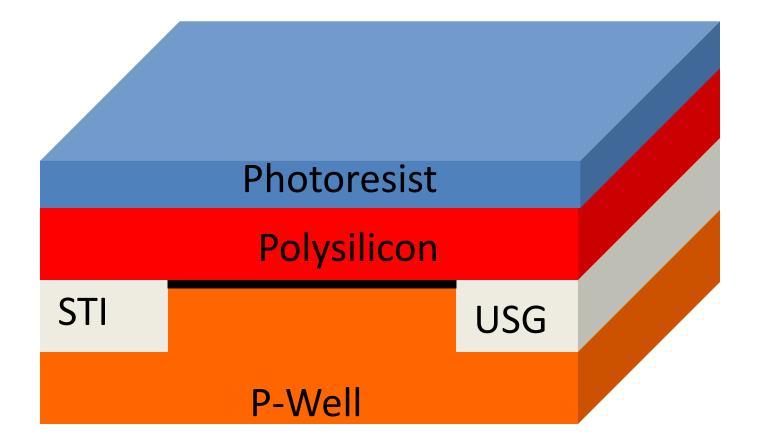


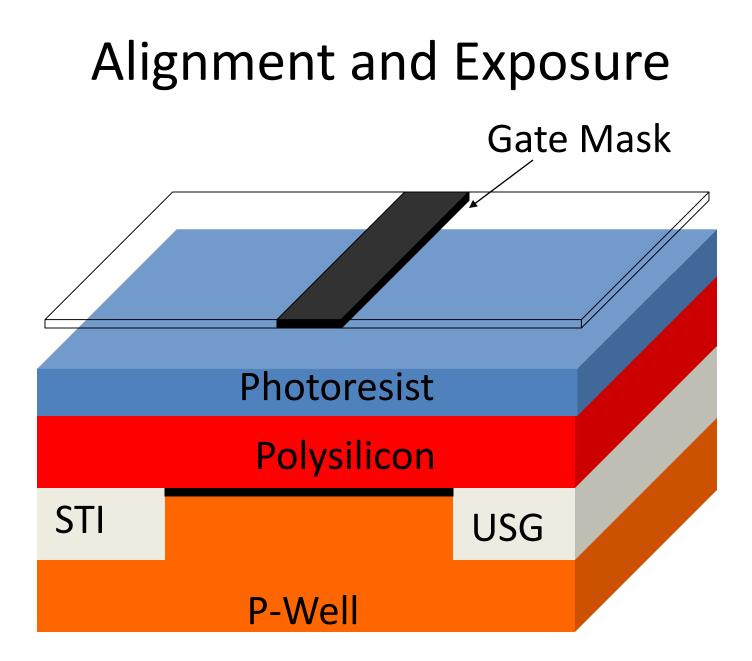


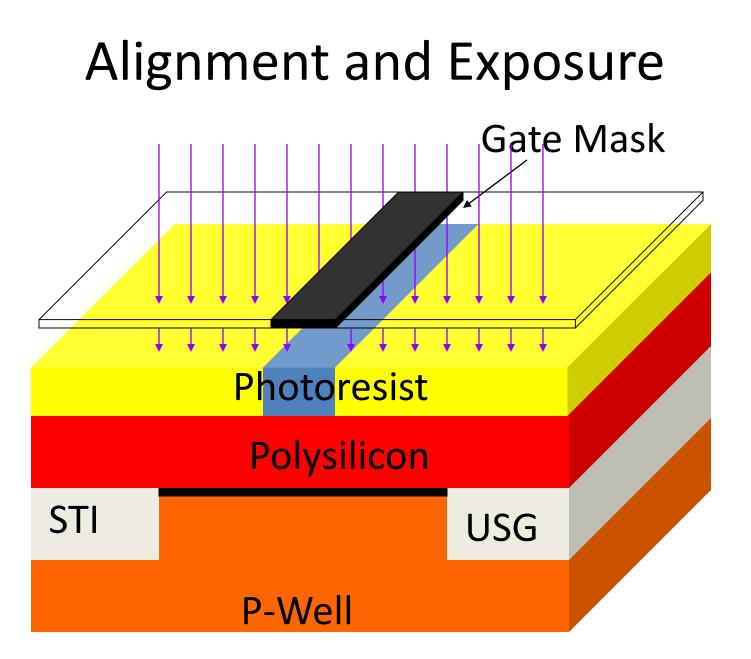




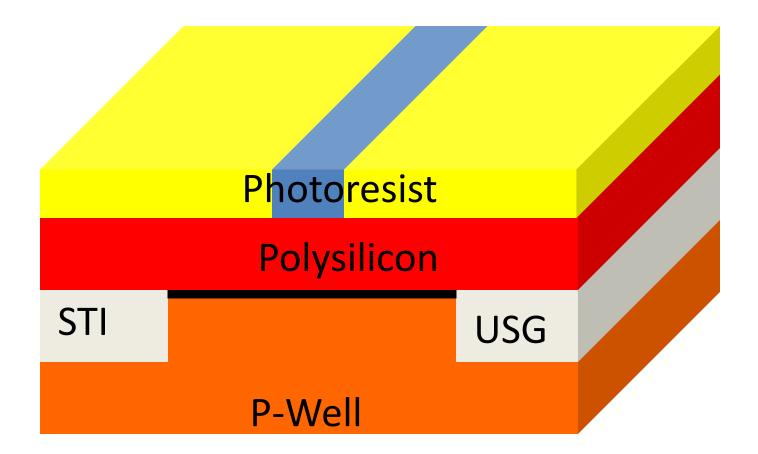




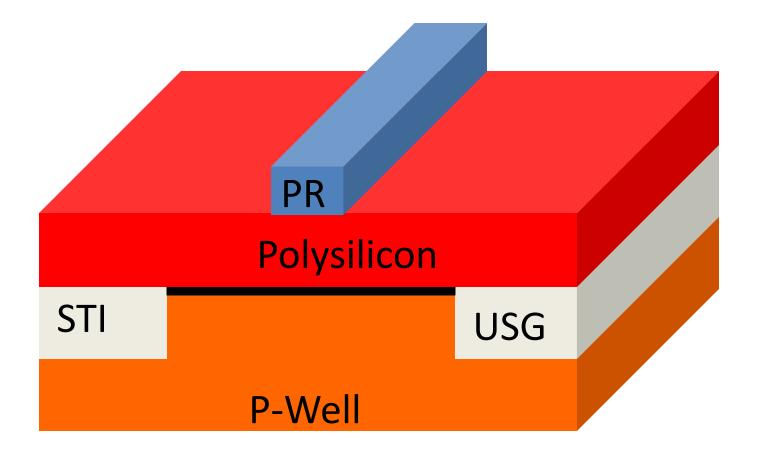




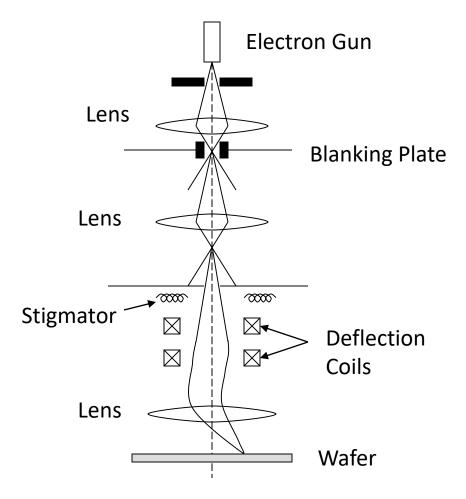
Post Exposure Bake



Development



Electron Beam Lithography System



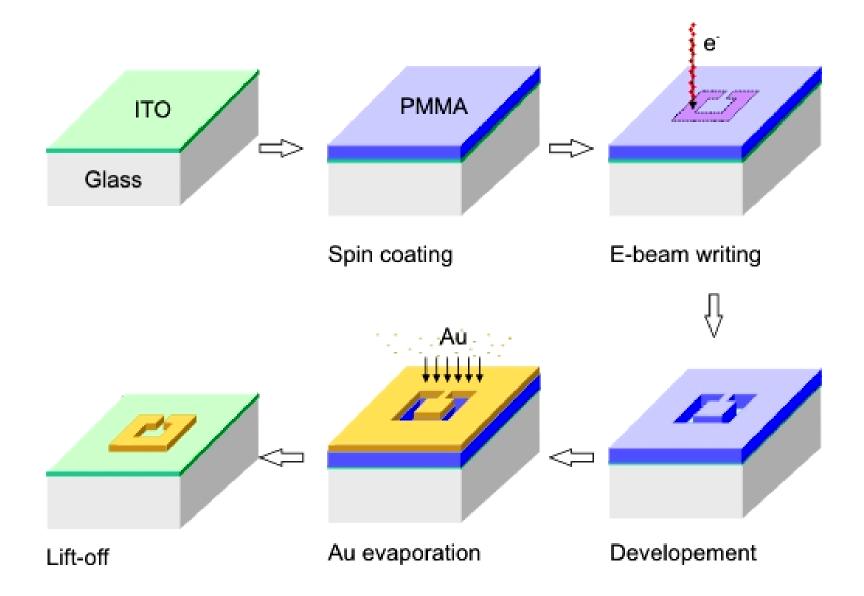
E – Beam Writing

Advantages

Better resolution Direct writing, no mask needed Arbitrary size, shape, order

Disadvantages

Serial process slow, small area Compatibility conducting, no high T process



Etching/remove photoresist

deposit thin film of desired material

1

3



4



coat and pattern photoresist

